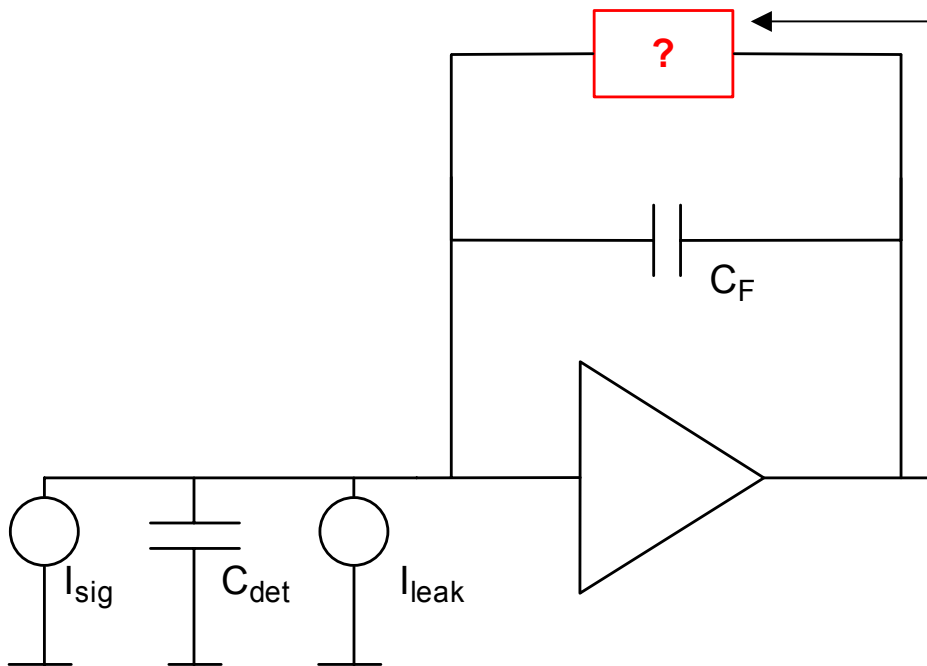


Charge-Sensitive Preamplifier Continuous Reset



Requirements:

- discharge C_F
- source I_{leak} (variable)
- minimum noise
- linear
- insensitive to process, temperature, and supply variation
- low capacitance

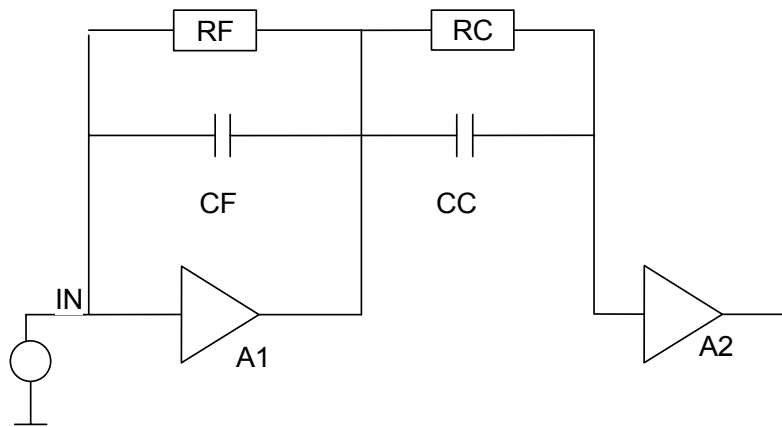
Simplest: FET

Drawback:

Nonlinear

Needs biasing

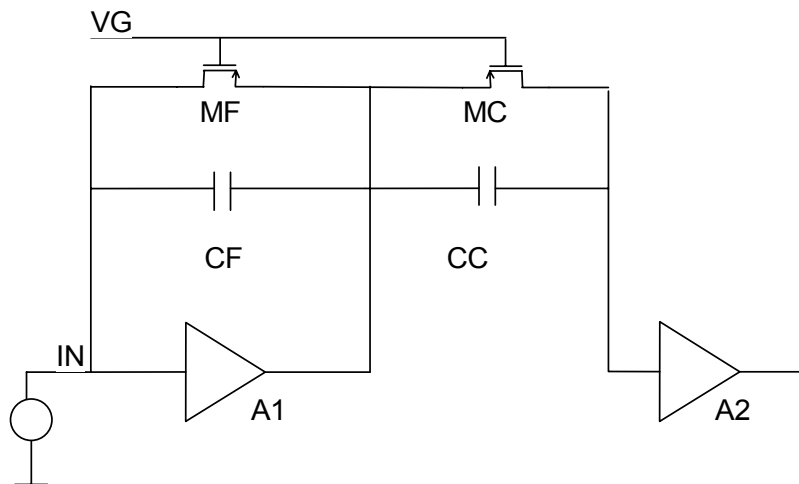
Nonlinear Pole-Zero Compensation



Classical

$$RF \cdot CF = RC \cdot CC$$

Zero created by RC, CC cancels pole formed by RF, CF



IC version

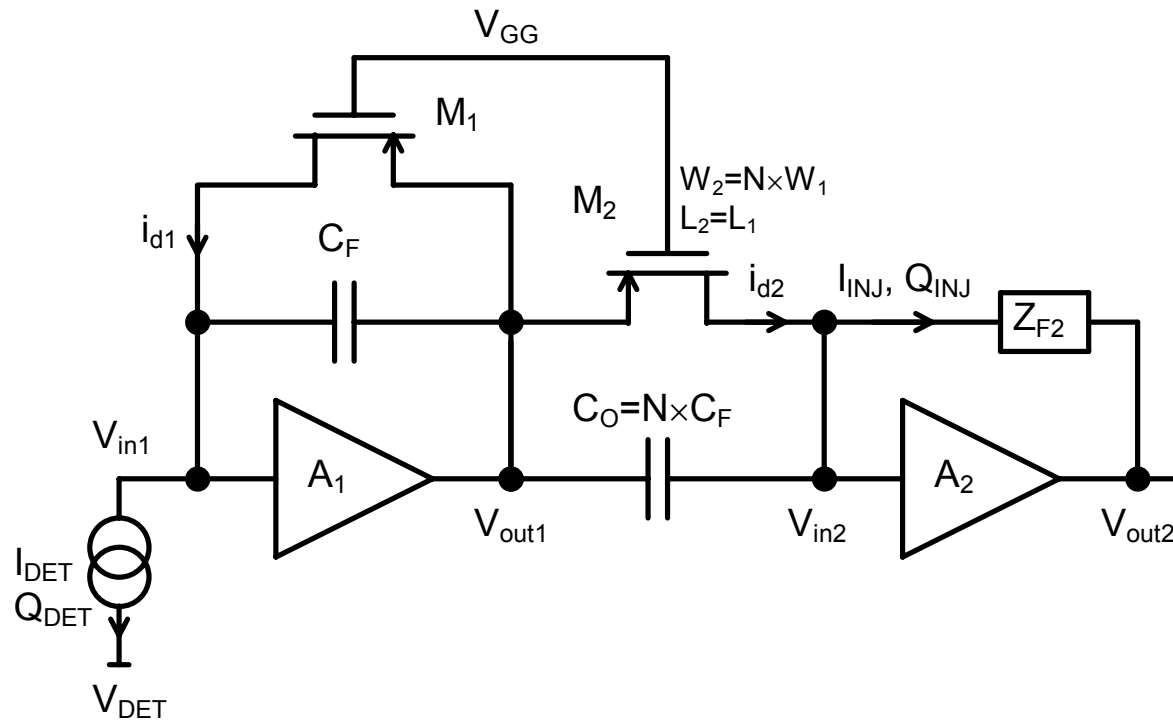
$$CC = N \cdot CF$$

$$(W/L)_{MC} = N \cdot (W/L)_{MF}$$

Zero created by MC, CC cancels pole formed by MF, CF

Rely on good matching characteristics of CMOS FETs and capacitors

In more detail...



$$V_{gs1} = V_{gs2}$$

$$V_{in1} = V_{in2}$$

$$V_{T1} = V_{T2}$$

$$I_{d1} = I_{DET}$$

$$I_{d2} = N \cdot I_{DET}$$

$$Q_{inj} = N \cdot Q_{DET}$$

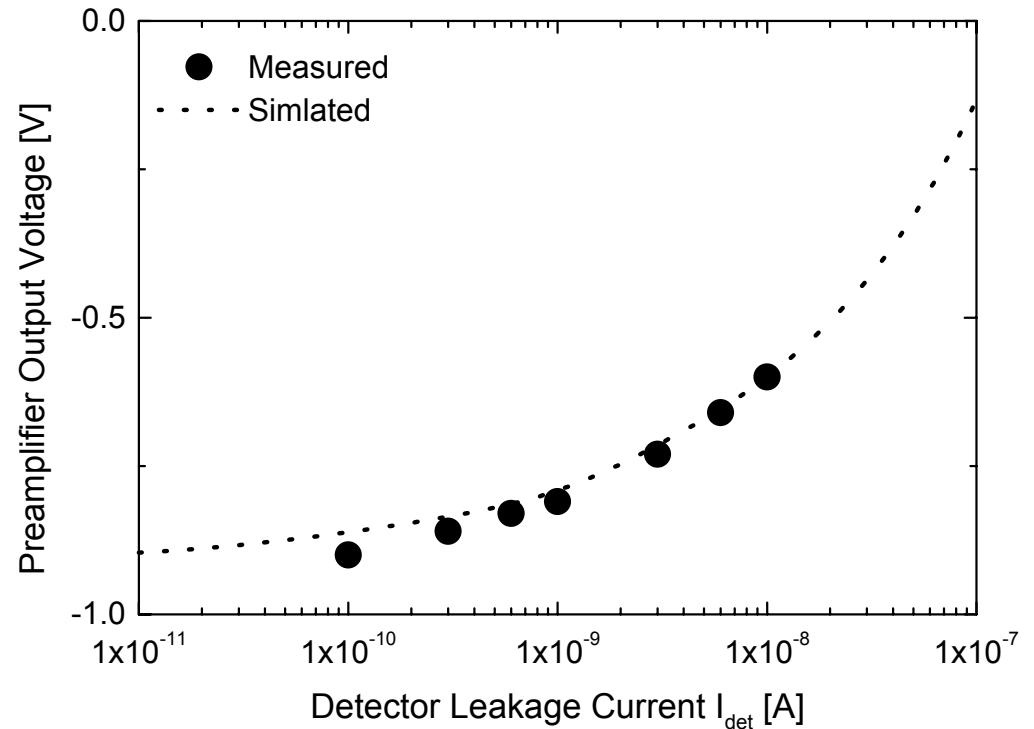
Composite amplifier is a charge (current) amplifier with gain of N

DC Analysis

M1, M2 in saturation, strong inversion

$$V_{\text{OUT}} \approx V_{\text{GG}} - V_{\text{T1}} + \sqrt{\frac{2}{k'} \frac{L_1}{W_1} (I_{\text{DET}} + I_{\text{B}})}$$

- Leakage current up to 100 nA can be sourced with modest increase in output voltage



Dynamic Analysis

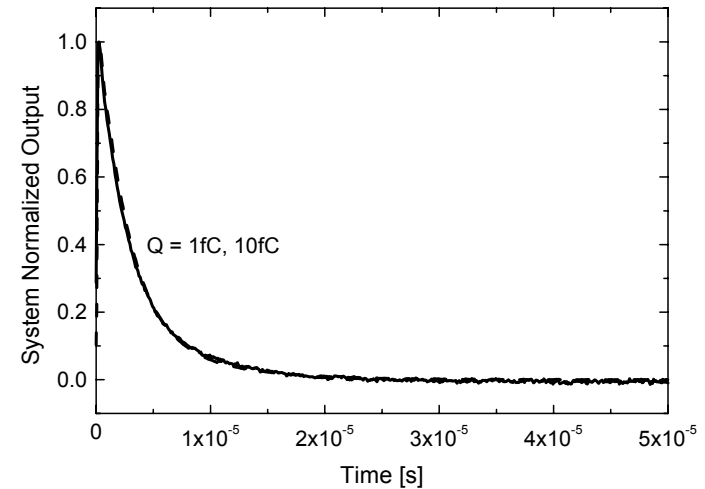
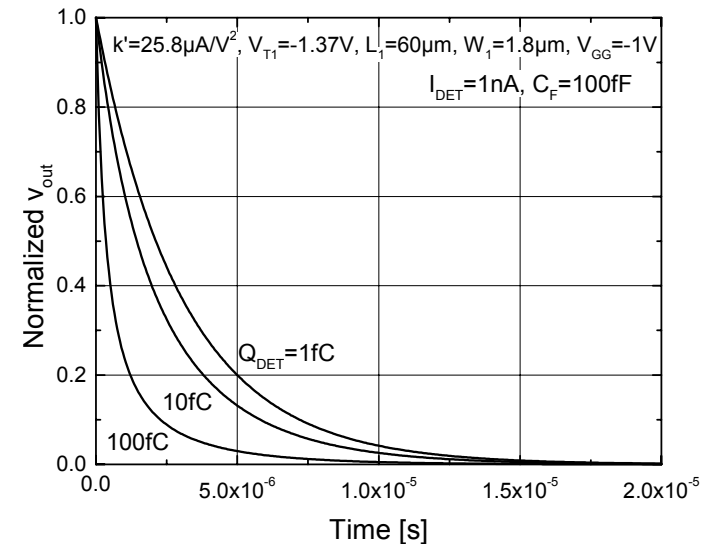
First stage alone

$$v_{out}(t) = \frac{2(V_{GS1} - V_{T1})}{\frac{K}{V_{GS1} - V_{T1}} \frac{C_F}{k'} \frac{L_1}{W_1} \exp\left[\frac{-t}{C_F} k' \frac{W_1}{L_1} (V_{GS1} - V_{T1})\right] + 1}$$

- Decay time constant $\sim C_F/g_{m1}$
- Effective feedback resistance of M1: $R_{F,eff} = 1/g_{m1}$
- Strong variation with Q_{DET}

With compensation

- Linearity is recovered
- Time constant no longer depends on injected charge



Noise Analysis

Parallel noise:

M1, M2 bias condition at minimum I_{DET} :

$V_{DS} > V_{GS} - V_T$ Saturation
 $(V_{GS} - V_T) \gg kT/q$ Strong Inversion

M1 contributes thermal noise < shot noise of detector leakage

$$ENC^2 = 2kTA_3t_m [\gamma g_{m1} \cdot (1 + g_{m1}/g_{mA}) + (\gamma g_{m2} + 1/R_{F2}) / N^2] + \text{series} + 1/f$$

Non-stationary noise:

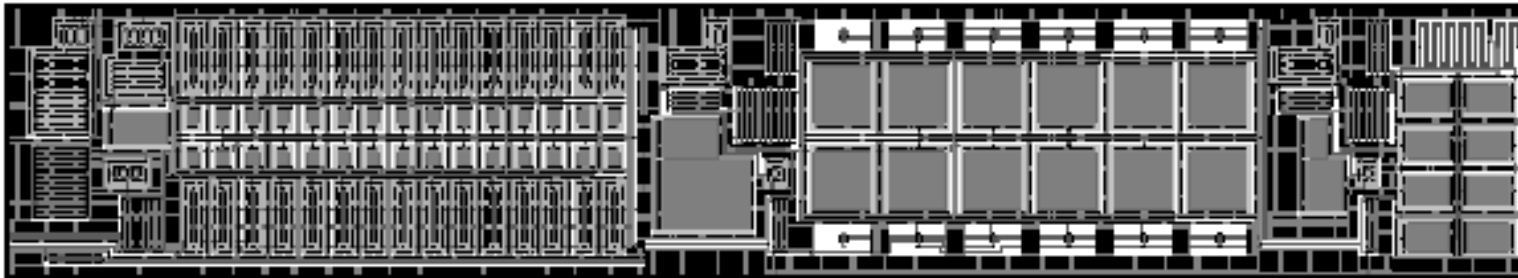
Due to increase in M1's drain current during the reset.

Signal-dependent $ENC_{NS} \sim \sqrt{Q_{DET}}$

Responsible for minor (< 2%) degradation of S/N.

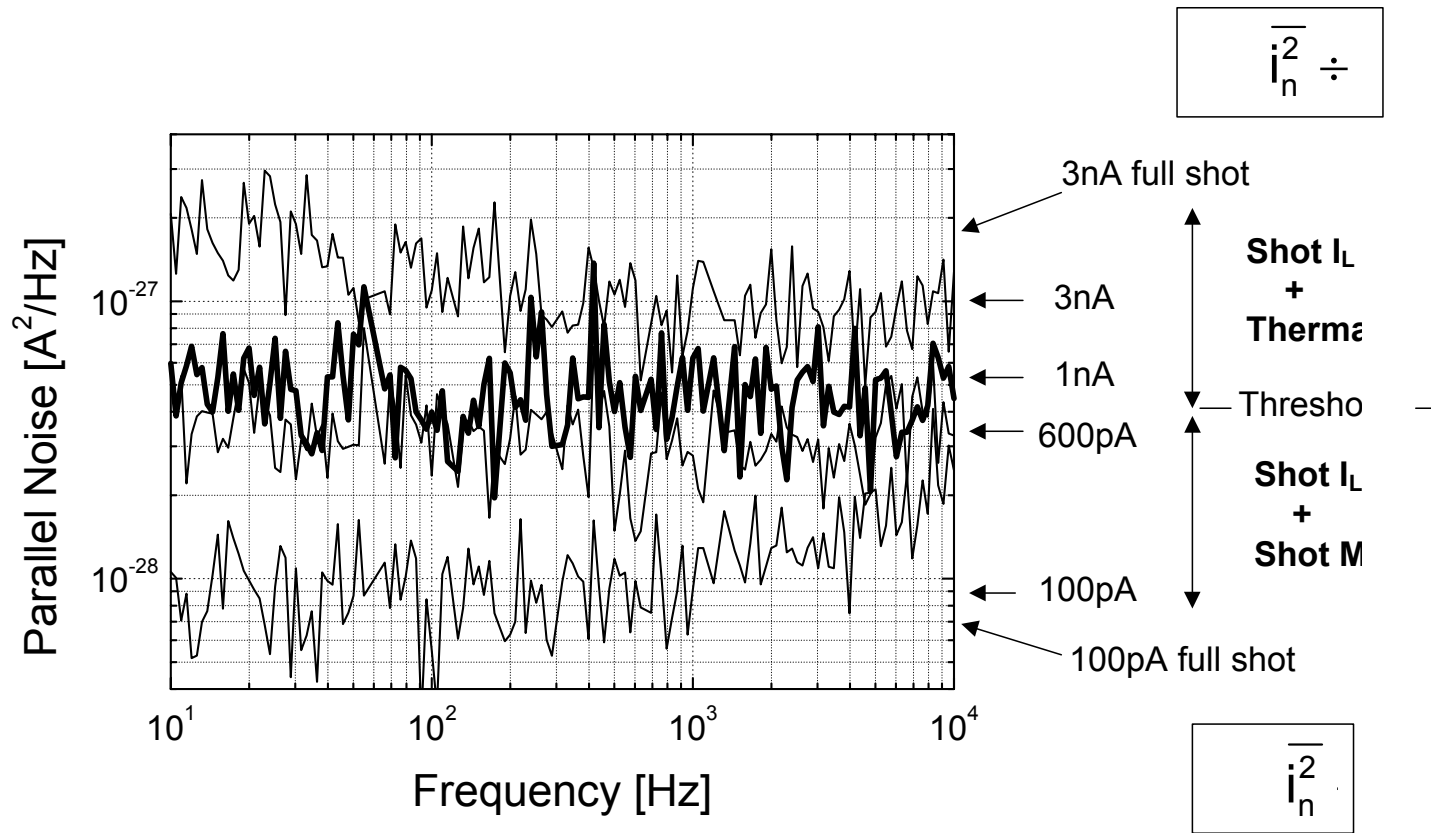
Layout

Two-stage compensation circuit
 $N_1 = 24$ (PMOS), $N_2 = 6$ (NMOS)
 $N_{\text{tot}} = 144$

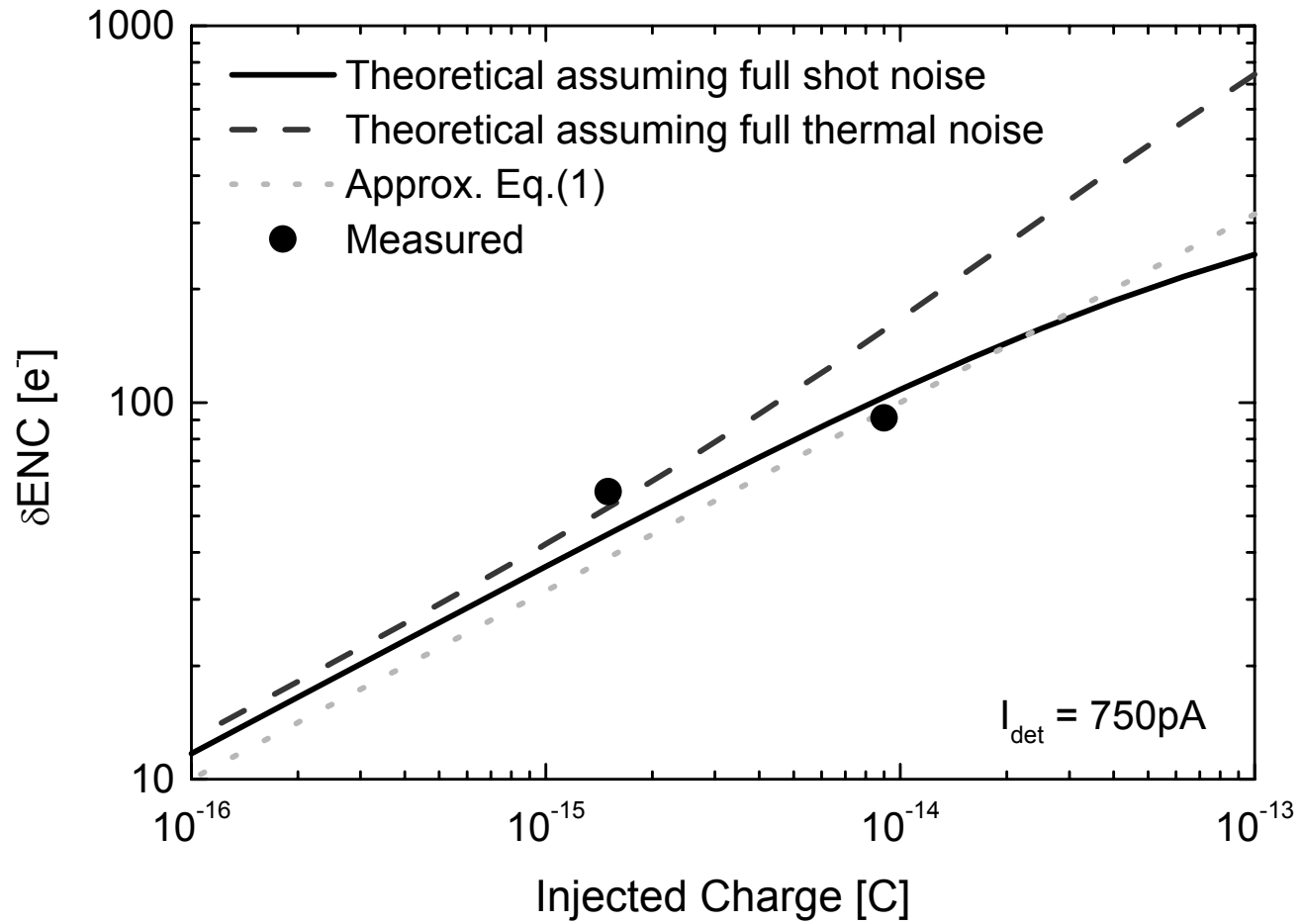


0.14 x 0.78 mm

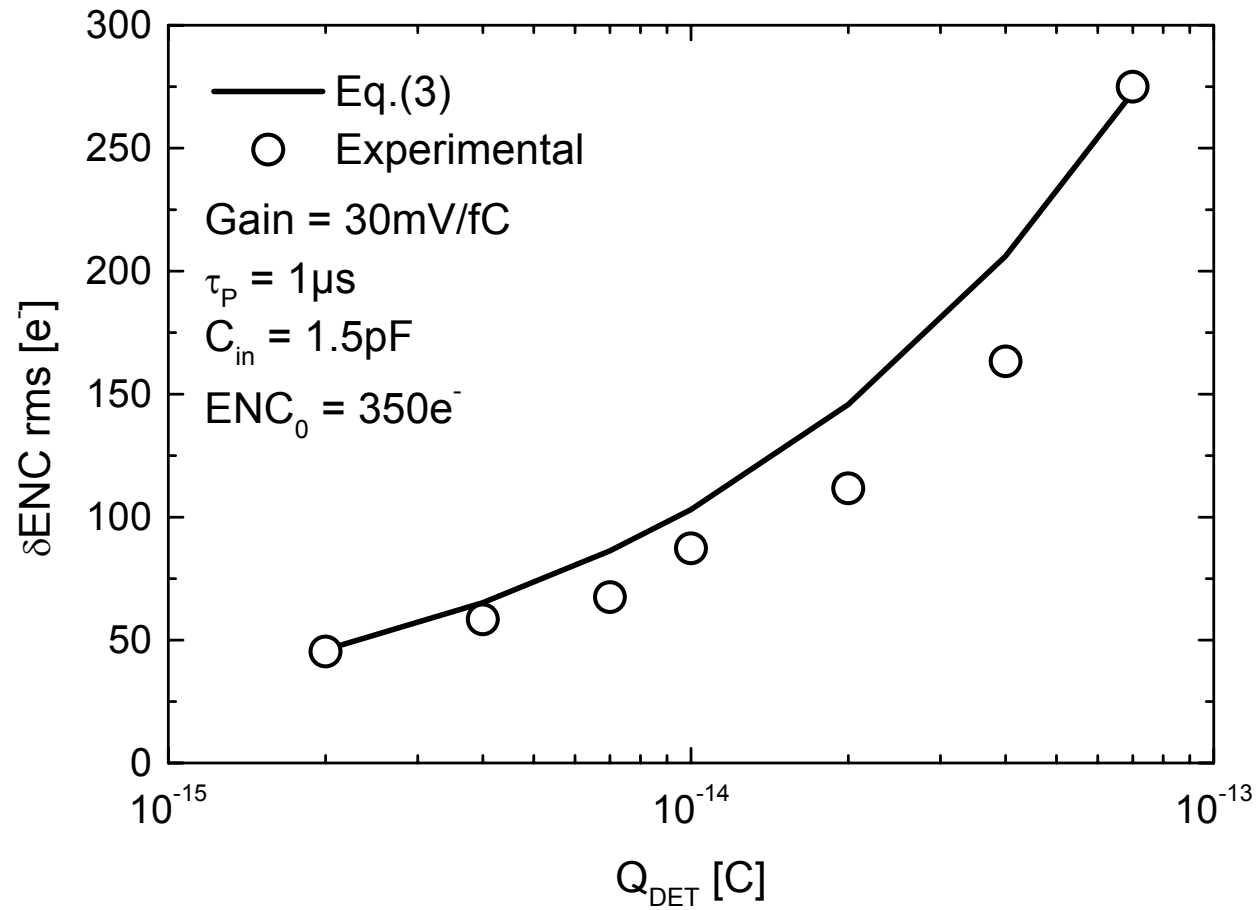
Parallel Noise



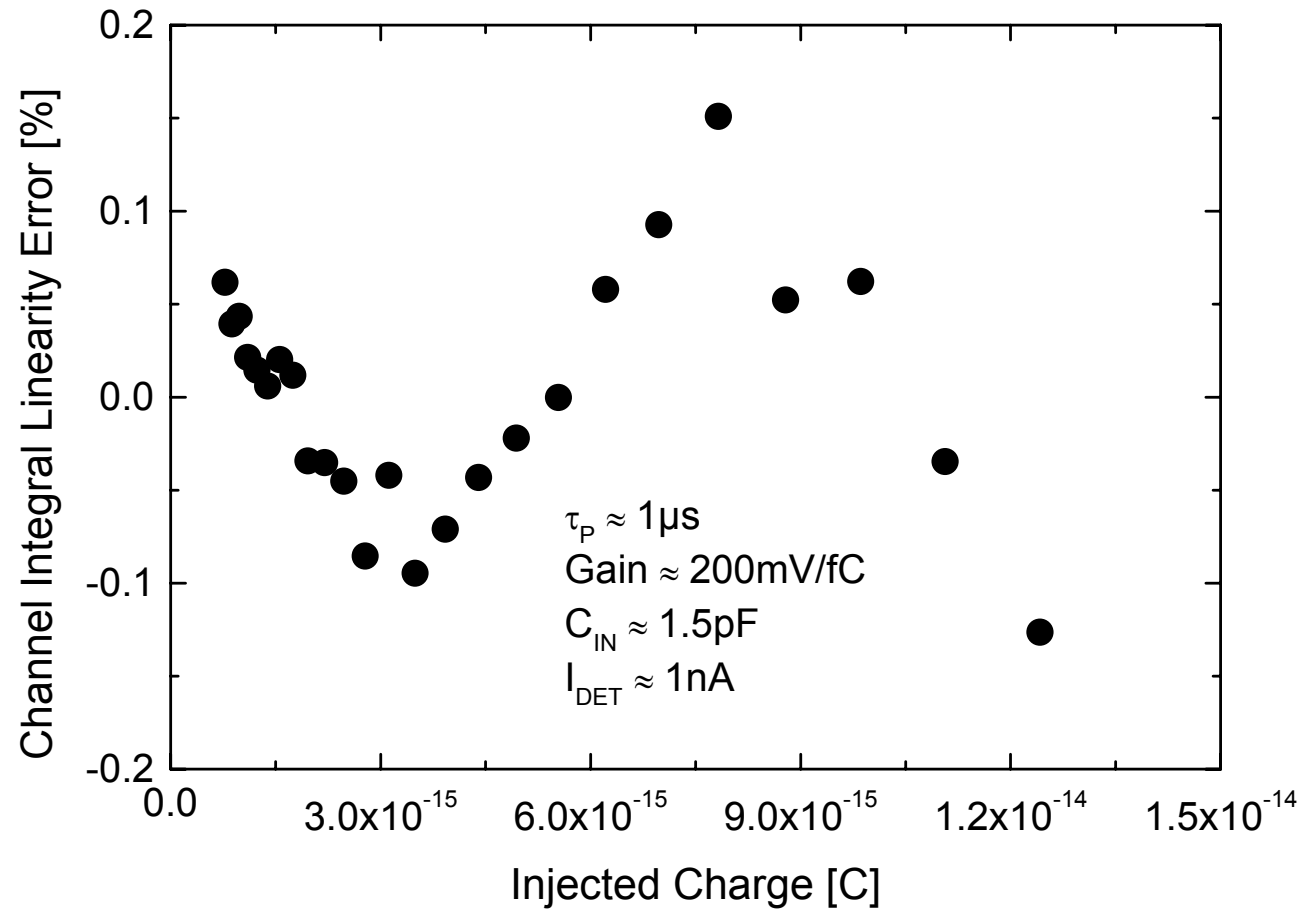
Nonstationary Noise



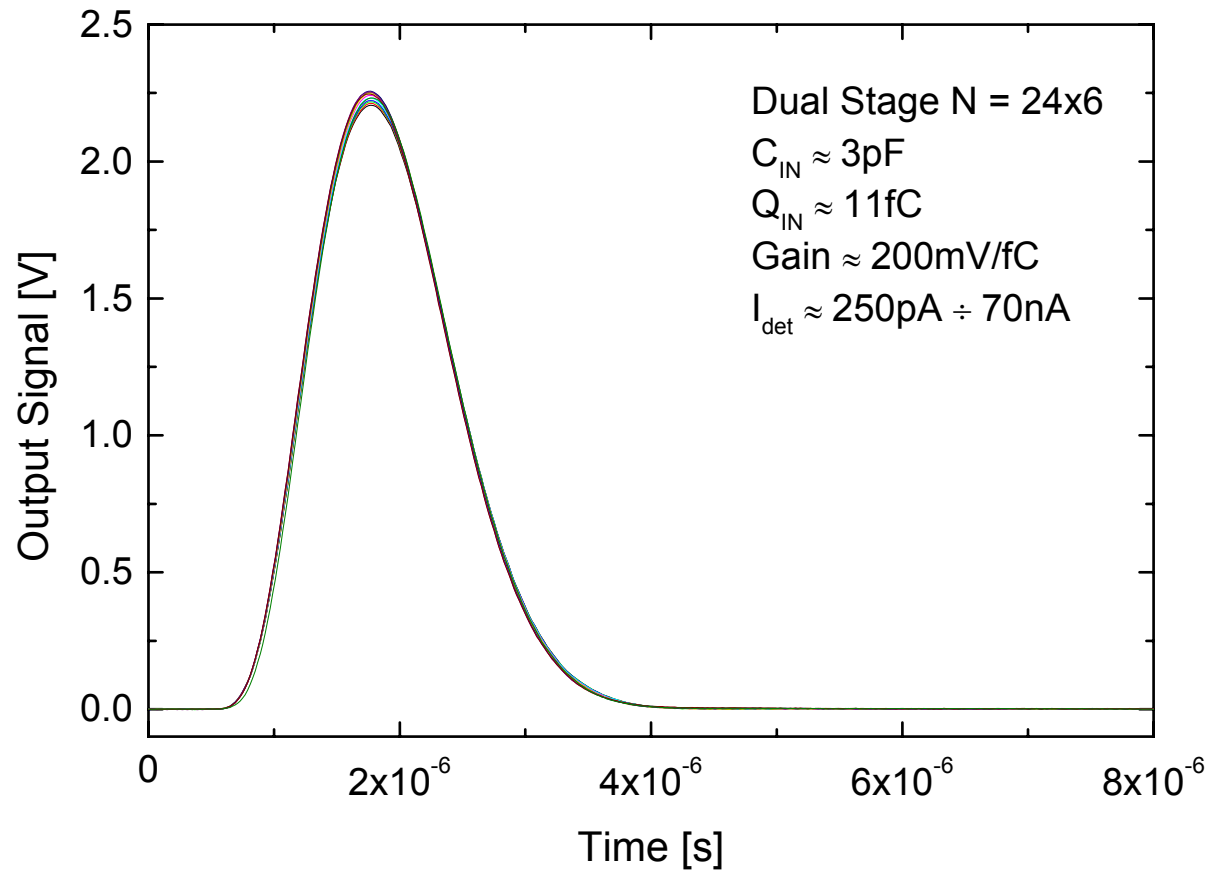
Nonstationary Noise



Nonlinearity



Leakage Current Handling



Summary

- New reset system for DC-coupled detectors
- Self-adaptive to wide range of leakage current
- No tweaking or switching
- Excellent noise and linearity
- Versatile

Shaping	5 th order compl. unip.
Gain	≈ 200mV/fC
Peaking time	≈ 400ns
ENC	≈ 30+37/pF+0.4√(Q/q)
Integral linearity error	< 0.2% @ 13fC